XC61G Series

ETR02003-005c

Low Voltage Detectors (V_{DF} = 0.8V~1.5V)
Standard Voltage Detectors (V_{DF} = 1.6V~6.0V)

■GENERAL DESCRIPTION

The XC61G series are highly precise, low power consumption voltage detectors, manufactured using CMOS and laser trimming technologies.

Detect voltage is extremely accurate with minimal temperature drift.

Both CMOS and N-ch open drain output configurations are available.

■APPLICATIONS

- ●Microprocessor reset circuitry
- ●Memory battery back-up circuits
- ●Power-on reset circuits
- ●Power failure detection
- ●System battery life and charge voltage monitors

■FEATURES

Highly Accurate : ±2%

Low Power Consumption : 0.7μA [VIN=1.5V]

Detect Voltage Range : 0.8V ~ 1.5V in 0.1V increments (Low Voltage)

: 1.6V ~ 6.0V in 0.1V increments (Standard Voltage)

Operating Voltage Range : 0.7V ~ 6.0V (Low Voltage)

: 0.7V ~ 10.0V (Standard Voltage)

Detect Voltage Temperature characteristics

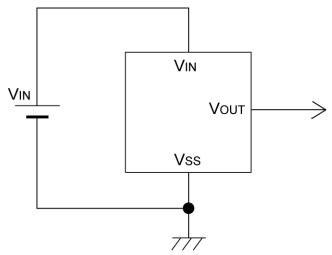
: ±100ppm/

Output Configuration : N-ch open drain output or CMOS

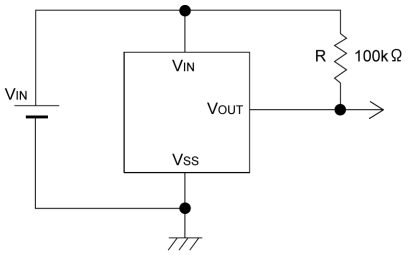
Operating Ambient Temperature : -40℃ ~ 85℃

Package : USP-3

■TYPICAL APPLICATION CIRCUITS



CMOS Output

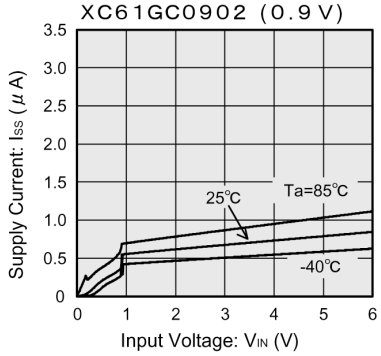


N-ch Open Drain Output

■TYPICAL PERFORMANCE CHARACTERISTICS

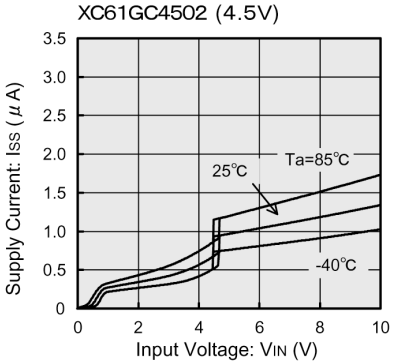
Supply Current vs. Input Voltage

XC61GC0902 (0.9V)

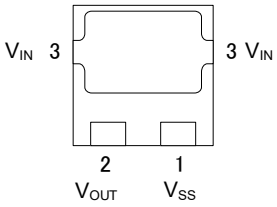


Supply Current vs. Input Voltage

XC61GC4502 (4.5V)



■PIN CONFIGURATION



(BOTTOM VIEW)

■PIN ASSIGNMENT

PIN NUMBER	PIN NAME	FUNCTION
USP-3		
3	VIN	Supply Voltage
1	VSS	Ground
2	VOUT	Output

■PRODUCT CLASSIFICATION

●Ordering Information

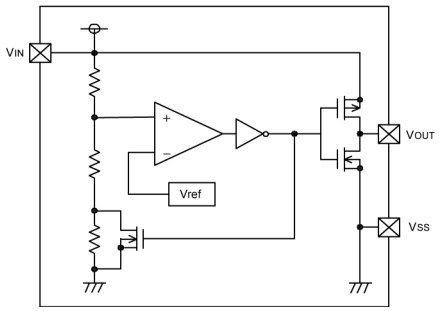
XC61G ①②③④⑤⑥⑦-⑧(*1)

DESIGNATOR	ITEM	SYMBOL	DESCRIPTION
①	Output Configuration	C	CMOS output
		N	N-ch open drain output
②③	Detect Voltage	08 ~ 60	e.g. 0.8V → ②0, ③8
			e.g. 1.5V → ②1, ③5
④	Output Delay	0	No delay
⑤	Detect Accuracy	2	±2%
⑥⑦-⑧	Packages (Order Unit)	HR-G	USP-3 (3,000pcs/Reel)

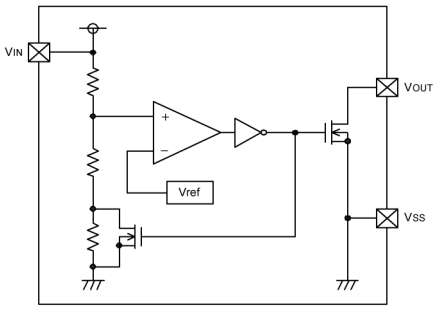
(*1) The “-G” suffix indicates that the products are Halogen and Antimony free as well as being fully RoHS compliant.

■BLOCK DIAGRAMS

(1) CMOS Output



(2) N-ch Open Drain Output



■ABSOLUTE MAXIMUM RATINGS

Ta = 25℃

PARAMETER			SYMBOL	RATINGS	UNITS
Input Voltage		*1	V_{IN}	V_{SS}-0.3 ~ 9.0	V
		*2		V_{SS}-0.3 ~ 12.0	
Output Current		*1	I_{OUT}	50	mA
		*2		50	
Output Voltage	CMOS		V_{OUT}	V_{SS} -0.3 ~ V_{IN} +0.3	V
	N-ch Open Drain Output *1			V_{SS} -0.3 ~ 9.0	
	N-ch Open Drain Output *2			V_{SS} -0.3 ~ 12.0	
Power Dissipation	USP-3		Pd	120	mW
Operating Ambient Temperature			Topr	-40 ~ 85	℃
Storage Temperature Range			Tstg	-40 ~ 125	℃

■ELECTRICAL CHARACTERISTICS

$V_{DF(T)}$ = 0.8 to 6.0V ± 2%

Ta=25℃

PARAMETER		SYMBOL	CONDITIONS		MIN.	TYP.	MAX.	UNITS	CIRCUITS
Detect Voltage		V_{DF}	$V_{DF(T)}$=0.8V~1.5V*1 $V_{DF(T)}$=1.6V~6.0V*2		V_{DF} x 0.98	V_{DF}	V_{DF} x 1.02	V	1
Hysteresis Range		V_{HYS}			V_{DF} x 0.02	V_{DF} x 0.05	V_{DF} x 0.08	V	1
Supply Current		I_{SS}	V_{IN} = 1.5V		-	0.7	2.3	μA	2
			V_{IN} = 2.0V		-	0.8	2.7		
			V_{IN} = 3.0V		-	0.9	3.0		
			V_{IN} = 4.0V		-	1.0	3.2		
			V_{IN} = 5.0V		-	1.1	3.6		
Operating Voltage		V_{IN}	$V_{DF(T)}$ = 0.8V to 1.5V		0.7	-	6.0	V	1
			$V_{DF(T)}$ = 1.6V to 6.0V		0.7	-	10.0		
Output Current (Low Voltage)		I_{OUT}	N-ch, V_{DS} = 0.5V	V_{IN} =0.7V	0.10	0.80	-	mA	3
				V_{IN} =1.0V	0.85	2.70	-		
			CMOS, P-ch, V_{DS}=2.1V	V_{IN} =6.0V	-	-7.5	-1.5		4
Output Current (Standard Voltage)			N-ch, V_{DS} = 0.5V	V_{IN} =1.0V	1.0	2.2	-		3
				V_{IN} =2.0V	3.0	7.7	-		
				V_{IN} =3.0V	5. 0	10.1	-		
				V_{IN} =4.0V	6.0	11.5	-		
				V_{IN} =5.0V	7.0	13.0	-		
			CMOS, P-ch, V_{DS}=2.1V	V_{IN} =8.0V	-	-10.0	-2.0		4
Leakage Current	CMOS Output (Pch)	I_{LEAK}	V_{IN}=V_{DF}x0.9, V_{OUT}=0V		-	-10	-	nA	3
	N-ch Open Drain		V_{IN}=6.0V, V_{OUT}=6.0V*1 V_{IN}=10.0V, V_{OUT}=10.0V*2		-	10	100		
Temperature Characteristics		ΔV_{DF}/ (ΔTopr·V_{DF})	-40℃≦Topr≦85℃		-	±100	-	ppm/℃	1
Delay Time (V_{DR} → V_{OUT} inversion)		t_{DLY}	V_{DR}→V_{OUT} inversion		-	0.03	0.2	ms	5

NOTE:
*1 : Low Voltage ($V_{DF(T)}$=0.8V~1.5V)
*2 : Standard Voltage ($V_{DF(T)}$=1.6V~~6.0V)
$V_{DF(T)}$: Nominal detect voltage
Release Voltage: V_{DR} = V_{DF} + V_{HYS}

■OPERATIONAL EXPLANATION

●CMOS output

① When input voltage (V_{IN}) is higher than detect voltage (V_{DF}), output voltage (V_{OUT}) will be equal to V_{IN}.
(A condition of high impedance exists with N-ch open drain output configurations.)

② When input voltage (V_{IN}) falls below detect voltage (V_{DF}), output voltage (V_{OUT}) will be equal to the ground voltage (V_{SS}) level.

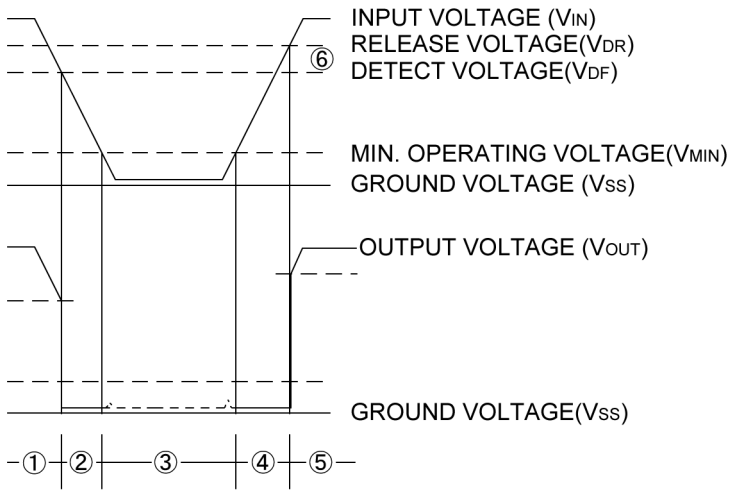
③ When input voltage (V_{IN}) falls to a level below that of the minimum operating voltage (V_{MIN}), output will become unstable. (As for the N-ch open drain product of XC61CN, the pull-up voltage goes out at the output voltage.)

④ When input voltage (V_{IN}) rises above the ground voltage (V_{SS}) level, output will be unstable at levels below the minimum operating voltage (V_{MIN}). Between the V_{MIN} and detect release voltage (V_{DR}) levels, the ground voltage (V_{SS}) level will be maintained.

⑤ When input voltage (V_{IN}) rises above detect release voltage (V_{DR}), output voltage (V_{OUT}) will be equal to V_{IN}.
(A condition of high impedance exists with N-ch open drain output configurations.)

⑥ The difference between V_{DR} and V_{DF} represents the hysteresis range.

●Timing Chart



■NOTES ON USE

1. Please use this IC within the stated absolute maximum ratings. For temporary, transitional voltage drop or voltage rising phenomenon, the IC is liable to malfunction should the ratings be exceeded.

2. When a resistor is connected between the V_{IN} pin and the power supply with CMOS output configurations, oscillation may occur as a result of voltage drops at R_{IN} if load current (I_{OUT}) exists. (refer to the Oscillation Description (1) below)

3. When a resistor is connected between the V_{IN} pin and the power supply with CMOS output configurations, irrespective of N-ch open-drain output configurations, oscillation may occur as a result of through current at the time of voltage release even If load current (I_{OUT}) does not exist. (refer to the Oscillation Description (2) below)

4. Please use N-ch open drain output configuration, when a resistor R_{IN} is connected between the V_{IN} pin and power source. In such cases, please ensure that R_{IN} is less than 10kΩ and that C is more than 0.1 μ F, please test with the actual device. (refer to the Oscillation Description (1) below)

5. With a resistor R_{IN} connected between the V_{IN} pin and the power supply, the V_{IN} pin voltage will be getting lower than the power supply voltage as a result of the IC's supply current flowing through the V_{IN} pin.

6. In order to stabilize the IC's operations, please ensure that V_{IN} pin input frequency's rise and fall times are more than 2μ s/ V.

7. Torex places an importance on improving our products and its reliability.
However, by any possibility, we would request user fail-safe design and post

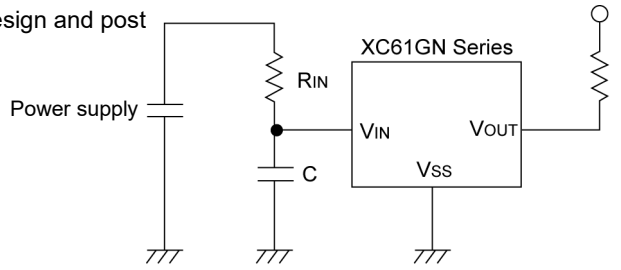


Figure 1: Circuit using an input resistor

●Oscillation Description

(1) Load current oscillation with the CMOS output configuration
When the voltage applied at power supply, release operations commence and the detector's output voltage increases. Load current (I_{OUT}) will flow at R_L. Because a voltage drop (R_{IN} x I_{OUT}) is produced at the R_{IN} resistor, located between the power supply and the V_{IN} pin, the load current will flow via the IC's V_{IN} pin. The voltage drop will also lead to a fall in the voltage level at the V_{IN} pin. When the V_{IN} pin voltage level falls below the detect voltage level, detect operations will commence. Following detect operations, load current flow will cease and since voltage drop at R_{IN} will disappear, the voltage level at the V_{IN} pin will rise and release operations will begin over again.
Oscillation may occur with this "release - detect - release" repetition.
Further, this condition will also appear via means of a similar mechanism during detect operations.

(2) Oscillation as a result of through current
Since the XC61G series are CMOS IC s, through current will flow when the IC's internal circuit switching operates (during release and detect operations). Consequently, oscillation is liable to occur as a result of drops in voltage at the through current's resistor (R_{IN}) during release voltage operations. (refer to Figure 3)
Since hysteresis exists during detect operations, oscillation is unlikely to occur.

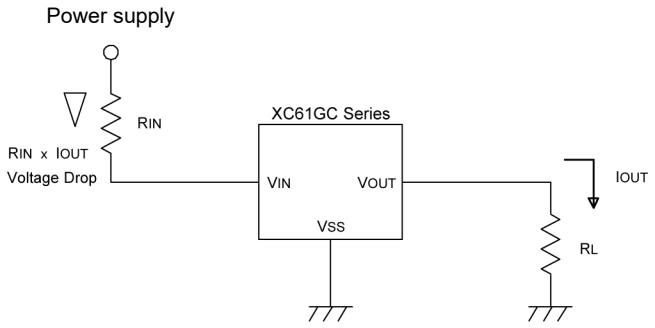


Figure 2: Oscillation in relation to output current

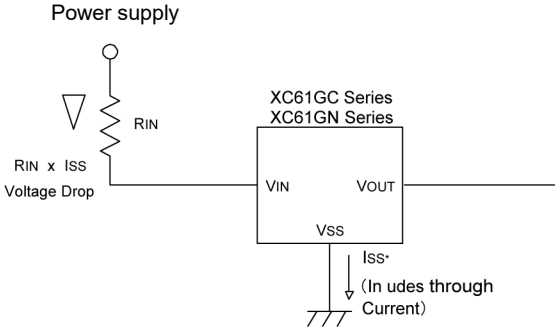
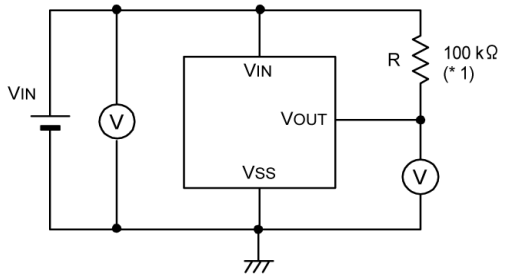


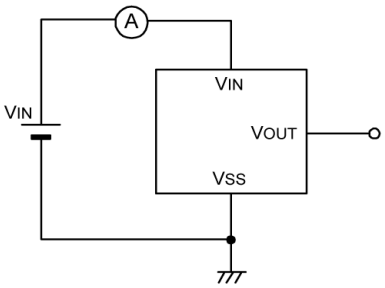
Figure 3: Oscillation in relation to through current

■TEST CIRCUITS

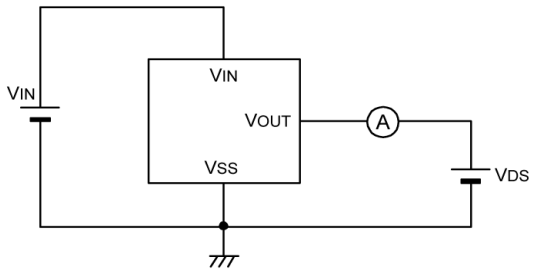
Circuit 1



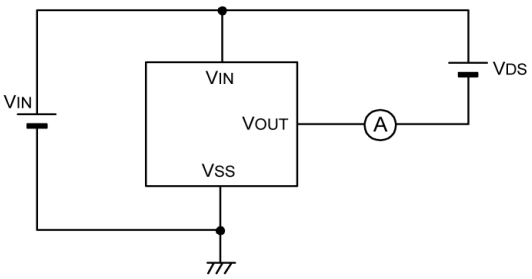
Circuit 2



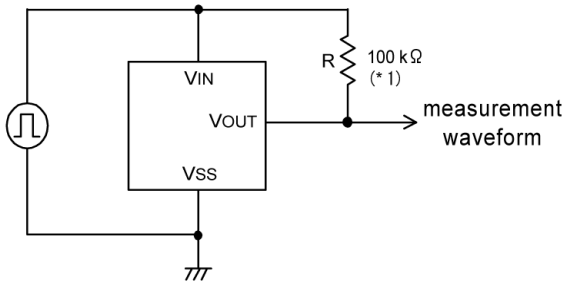
Circuit 3



Circuit 4



Circuit 5

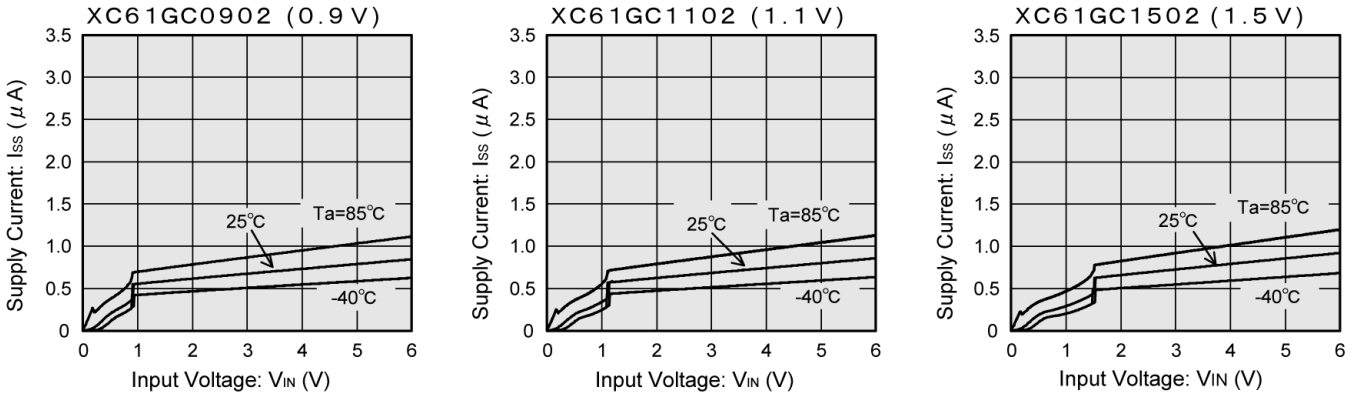


* 1 : The resistor is not necessary with CMOS output products.

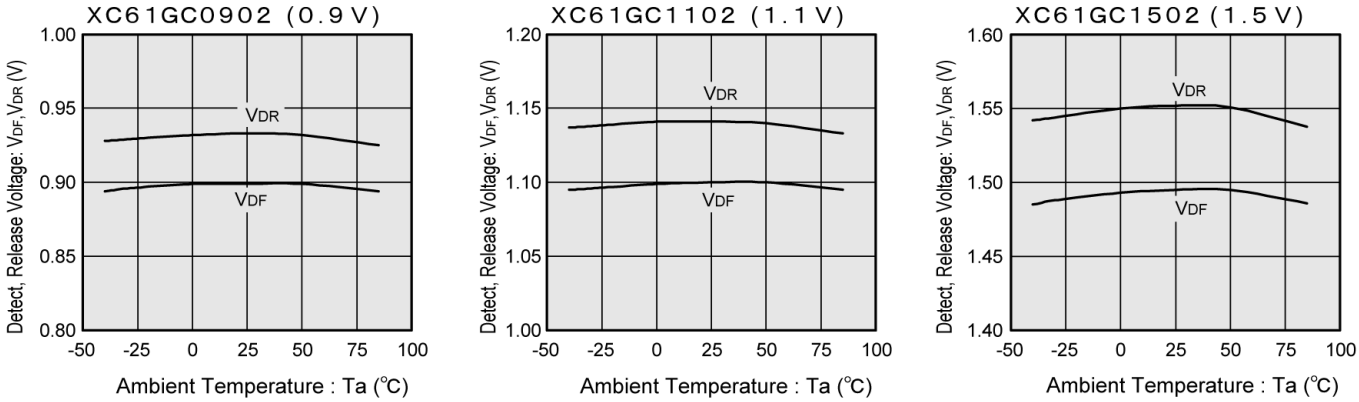
■TYPICAL PERFORMANCE CHARACTERISTICS

●Low Voltage

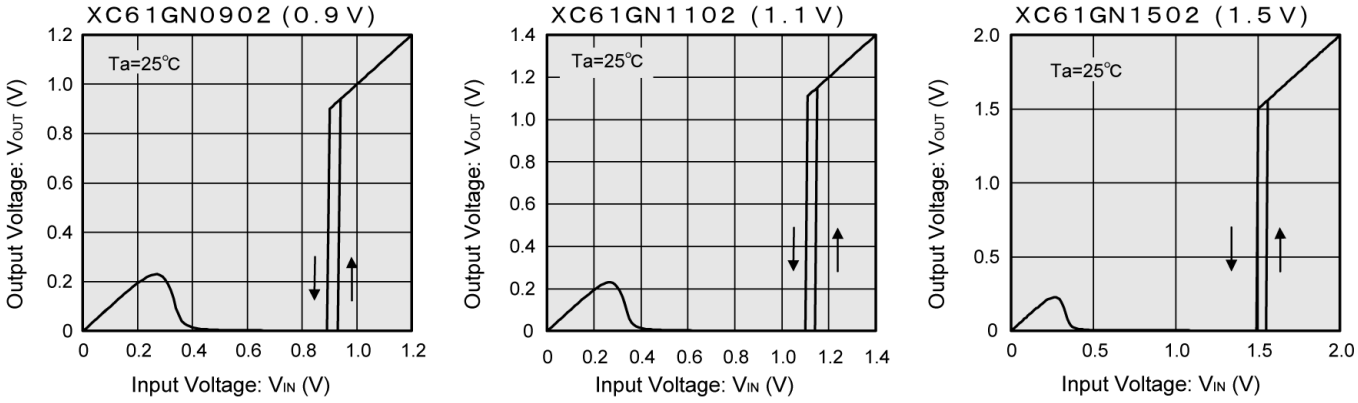
(1) Supply Current vs. Input Voltage



(2) Detect, Release Voltage vs. Ambient Temperature



(3) Output Voltage vs. Input Voltage



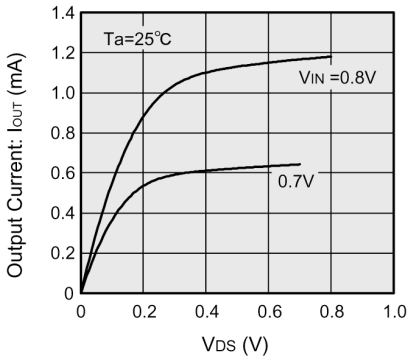
Note: Unless otherwise stated, the N-ch open drain pull-up resistance value is 100kΩ.

■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

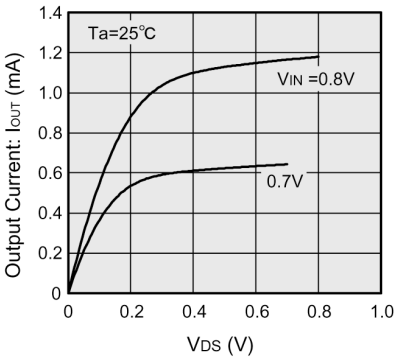
●Low Voltage (Continued)

(4) N-ch Driver Output Current vs. VDS

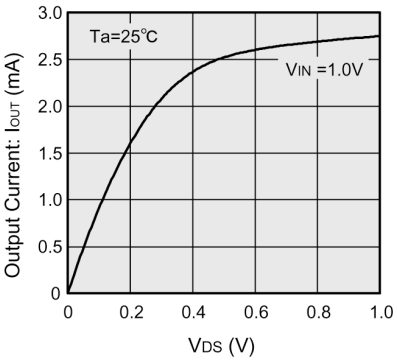
XC61GC0902 (0.9V)



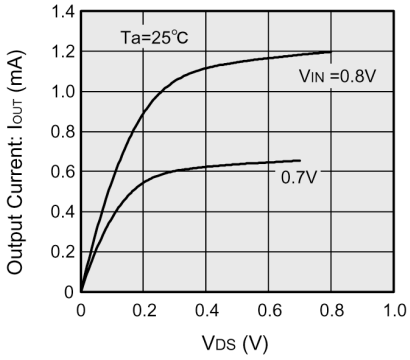
XC61GC1102 (1.1V)



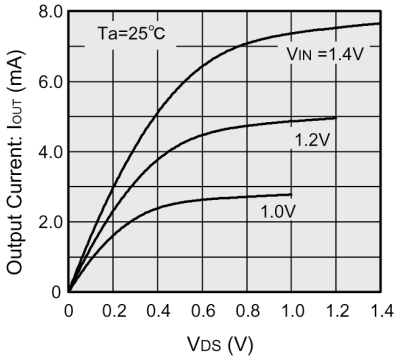
XC61GC1102 (1.1V)



XC61GC1502 (1.5V)

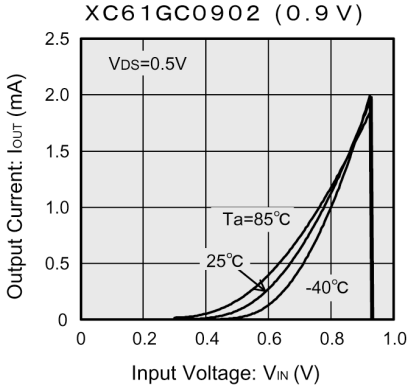


XC61GC1502 (1.5V)

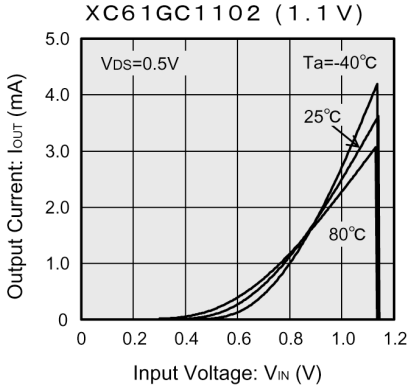


(5) N-ch Driver Output Current vs. Input Voltage

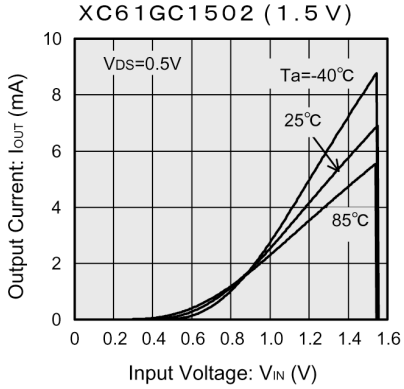
XC61GC0902 (0.9V)



XC61GC1102 (1.1V)

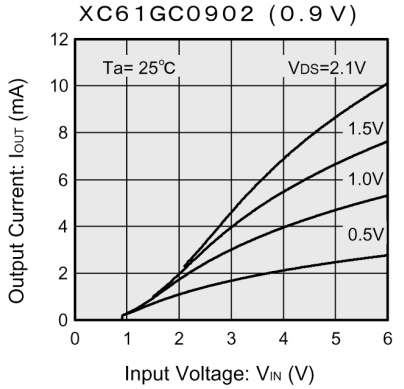


XC61GC1502 (1.5V)

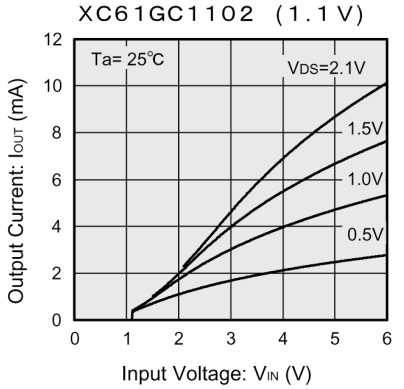


(6) P-ch Driver Output Current vs. Input Voltage

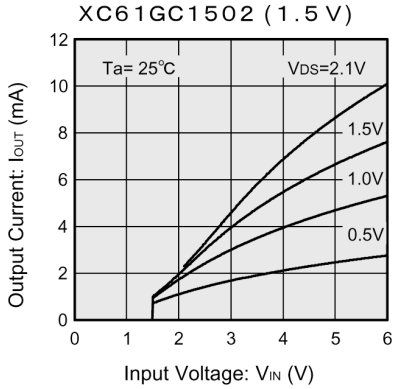
XC61GC0902 (0.9V)



XC61GC1102 (1.1V)



XC61GC1502 (1.5V)

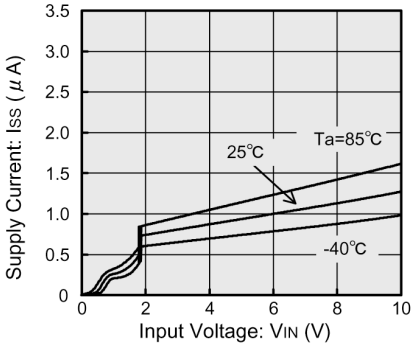


■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

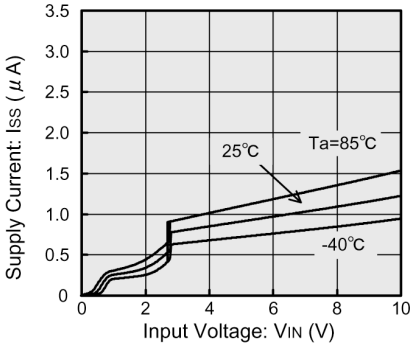
●Standard Voltage

(1) Supply Current vs. Input Voltage

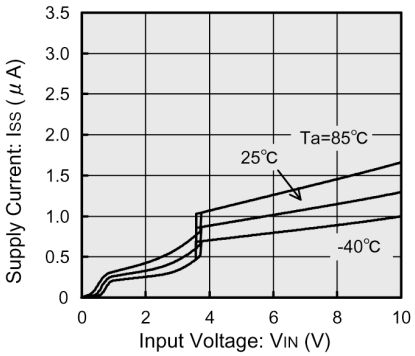
XC61GC1802 (1.8V)



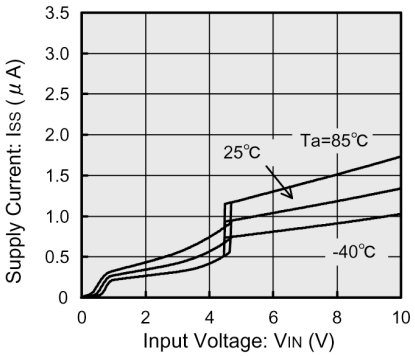
XC61GC2702 (2.7V)



XC61GC3602 (3.6V)

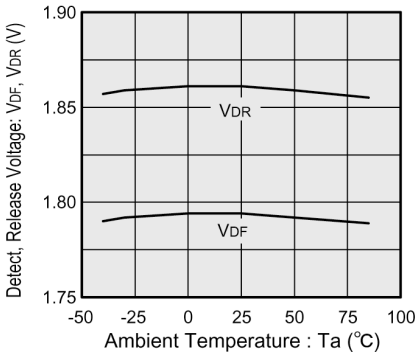


XC61GC4502 (4.5V)

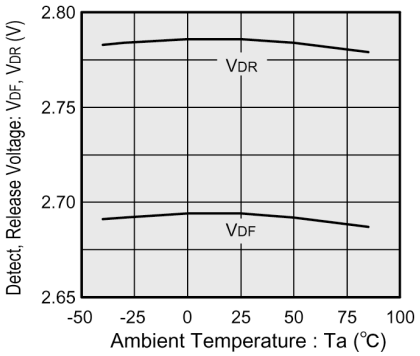


(2) Detect, Release Voltage vs. Ambient Temperature

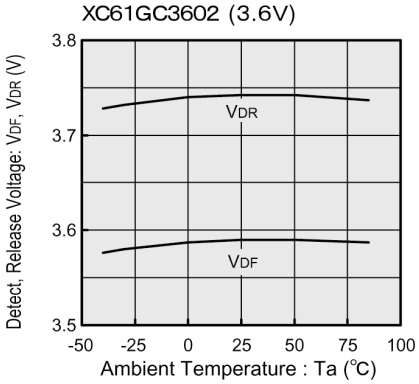
XC61GC1802 (1.8V)



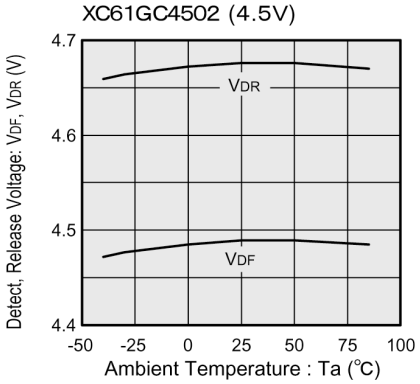
XC61GC2702 (2.7V)



XC61GC3602 (3.6V)



XC61GC4502 (4.5V)

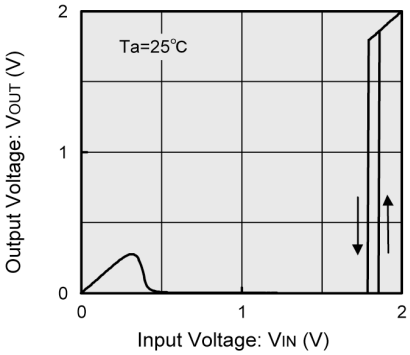


■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

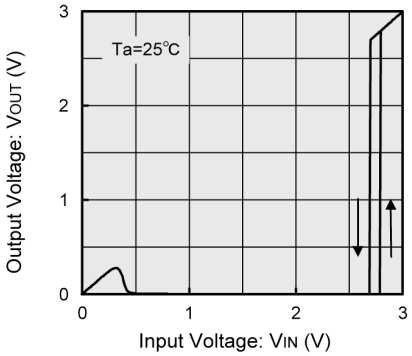
●Standard Voltage (Continued)

(3) Output Voltage vs. Input Voltage

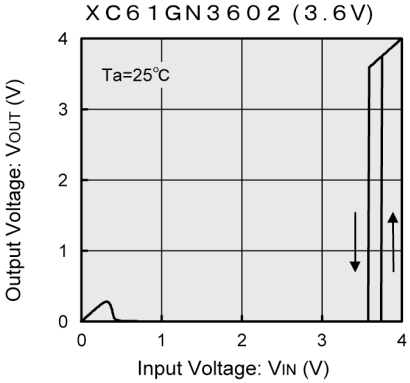
XC61GN1802 (1.8V)



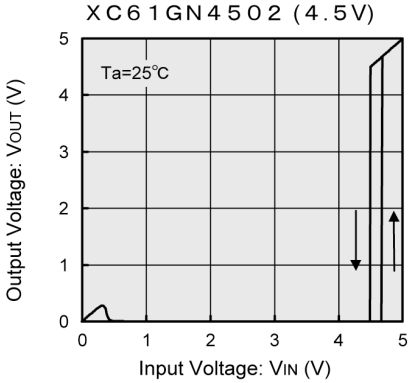
XC61GN2702 (2.7V)



XC61GN3602 (3.6V)



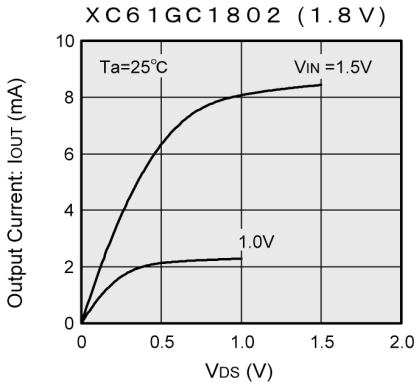
XC61GN4502 (4.5V)



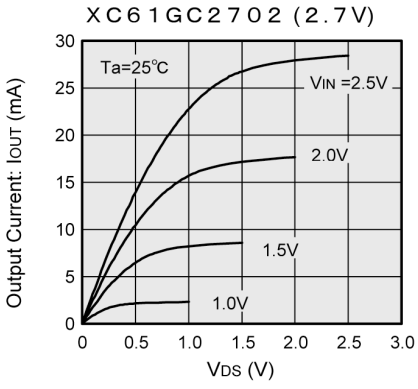
Note: Unless otherwise stated, the N-ch open drain pull-up resistance value is 100kΩ.

(4) N-ch Driver Output Current vs. VDS

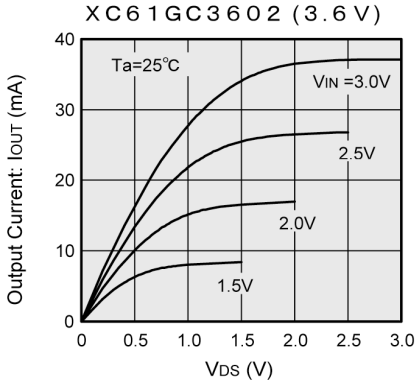
XC61GC1802 (1.8V)



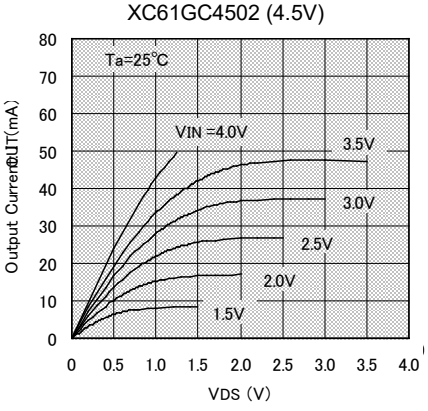
XC61GC2702 (2.7V)



XC61GC3602 (3.6V)



XC61GC4502 (4.5V)

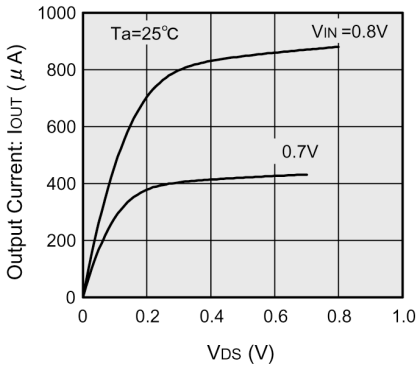


■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

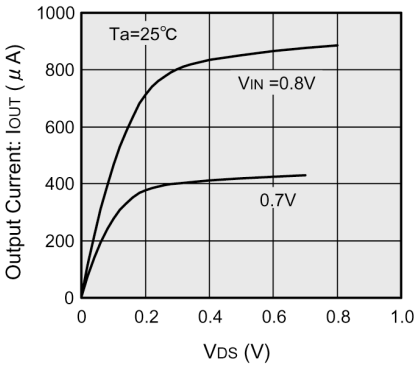
●Standard Voltage (Continued)

(4) N-ch Driver Output Current vs. VDS

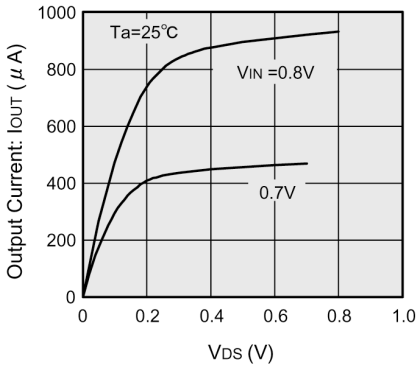
XC61GC1802 (1.8V)



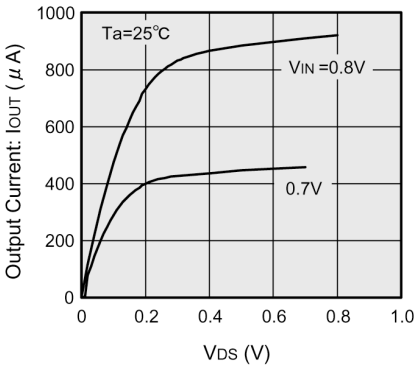
XC61GC2702 (2.7V)



XC61GC3602 (3.6V)

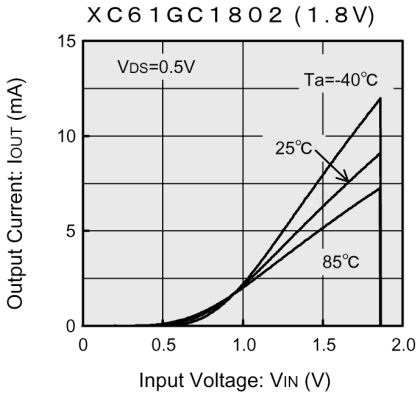


XC61GC4502 (4.5V)

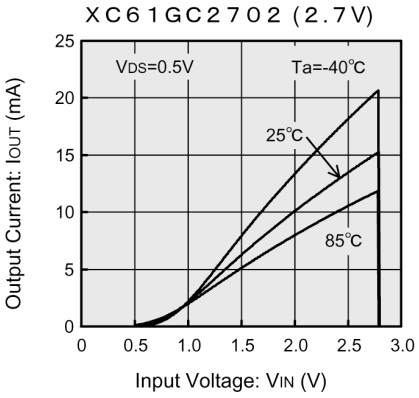


(5) N-ch Driver Output Current vs. Input Voltage

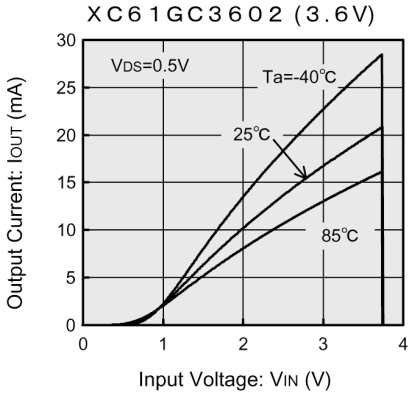
XC61GC1802 (1.8V)



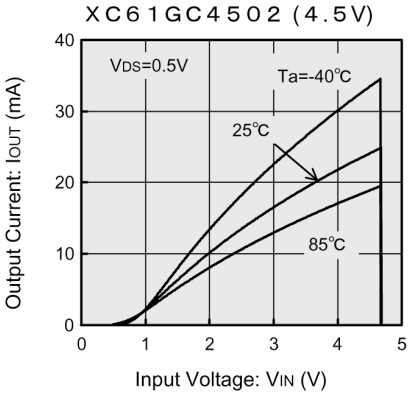
XC61GC2702 (2.7V)



XC61GC3602 (3.6V)



XC61GC4502 (4.5V)

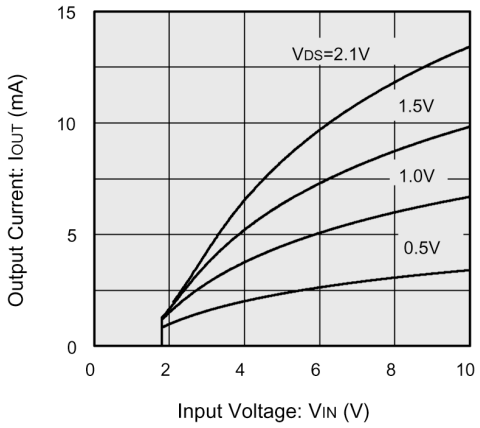


■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

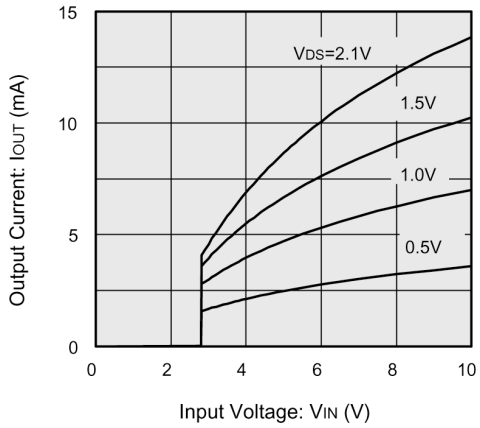
●Standard Voltage (Continued)

(6) P-ch Driver Output Current vs. Input Voltage

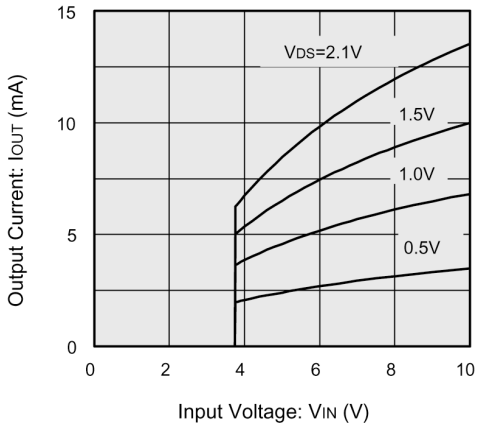
XC61GC1802 (1.8V)



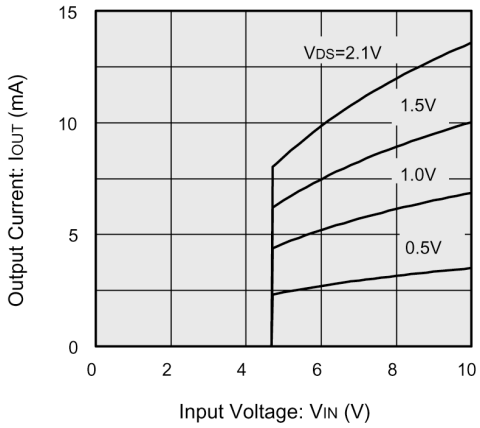
XC61GC2702 (2.7V)



XC61GC3602 (3.6V)



XC61GC4502 (4.5V)



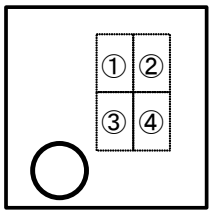
■PACKAGING INFORMATION

For the latest package information go to, www.torexsemi.com/technical-support/packages

PACKAGE	OUTLINE / LAND PATTERN	THERMAL CHARACTERISTICS
USP-3	USP-3 PKG	USP-3 Power Dissipation

■MARKING RULE

●USP-3



USP-3
(TOP VIEW)

① represents integer of output voltage and detect voltage

CMOS Output (XC61GC series)

MARK	VOLTAGE (V)
A	0.X
B	1.X
C	2.X
D	3.X
E	4.X
F	5.X
H	6.X

N-ch Open Drain Output (XC61GN series)

MARK	VOLTAGE (V)
K	0.X
L	1.X
M	2.X
N	3.X
P	4.X
R	5.X
S	6.X

② represents decimal number of detect voltage

Ex:

MARK	VOLTAGE (V)	PRODUCT SERIES
3	X.3	XC61G**3
0	X.0	XC61G**0

③ represents delay time

MARK	Delay Time	PRODUCT SERIES
3	No	XC61G***0

④ represents production lot number
0 to 9,A to Z reverse character 0 to 9, A to Z repeated
(G, I, J, O, Q, W excluded)

1. The product and product specifications contained herein are subject to change without notice to improve performance characteristics. Consult us, or our representatives before use, to confirm that the information in this datasheet is up to date.

2. The information in this datasheet is intended to illustrate the operation and characteristics of our products. We neither make warranties or representations with respect to the accuracy or completeness of the information contained in this datasheet nor grant any license to any intellectual property rights of ours or any third party concerning with the information in this datasheet.

3. Applicable export control laws and regulations should be complied and the procedures required by such laws and regulations should also be followed, when the product or any information contained in this datasheet is exported.

4. The product is neither intended nor warranted for use in equipment of systems which require extremely high levels of quality and/or reliability and/or a malfunction or failure which may cause loss of human life, bodily injury, serious property damage including but not limited to devices or equipment used in 1) nuclear facilities, 2) aerospace industry, 3) medical facilities, 4) automobile industry and other transportation industry and 5) safety devices and safety equipment to control combustions and explosions. Do not use the product for the above use unless agreed by us in writing in advance.

5. Although we make continuous efforts to improve the quality and reliability of our products; nevertheless Semiconductors are likely to fail with a certain probability. So in order to prevent personal injury and/or property damage resulting from such failure, customers are required to incorporate adequate safety measures in their designs, such as system fail safes, redundancy and fire prevention features.

6. Our products are not designed to be Radiation-resistant.

7. Please use the product listed in this datasheet within the specified ranges.

8. We assume no responsibility for damage or loss due to abnormal use.

9.

TOREX SEMICONDUCTOR LTD.